

<b>Interview Summary</b>	<b>Application No.</b>	<b>Applicant(s)</b>	
	08/169,127	SHINOHARA ET AL.	
	<b>Examiner</b>	<b>Art Unit</b>	
	Marianne L. Padgett	1762	

All participants (applicant, applicant's representative, PTO personnel):

(1) Marianne L. Padgett.

(3) Jon Guay & Ryosuka Murata.

(2) Jeff Costellia & Kasumi Tanitsu.

(4) Kunitaka Yamamoto & Kiyashi Shinohara.

Date of Interview: 06 June 2007.

Type: a) ☐ Telephonic b) ☐ Video Conference  
c) ☒ Personal [copy given to: 1) ☐ applicant 2) ☒ applicant's representative]

Exhibit shown or demonstration conducted: d) ☐ Yes e) ☒ No.  
If Yes, brief description: \_\_\_\_\_.

Claim(s) discussed: 61,71,76,140,144,151,153,164,165,168 and 176-180.

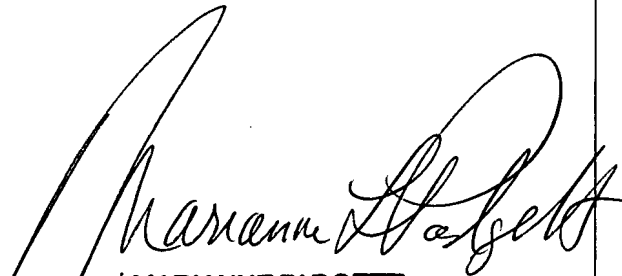
Identification of prior art discussed: US PN 6,261,856 B1.

Agreement with respect to the claims f) ☐ was reached. g) ☒ was not reached. h) ☐ N/A.

Substance of Interview including description of the general nature of what was agreed to if an agreement was reached, or any other comments: See Continuation Sheet.

(A fuller description, if necessary, and a copy of the amendments which the examiner agreed would render the claims allowable, if available, must be attached. Also, where no copy of the amendments that would render the claims allowable is available, a summary thereof must be attached.)

THE FORMAL WRITTEN REPLY TO THE LAST OFFICE ACTION MUST INCLUDE THE SUBSTANCE OF THE INTERVIEW. (See MPEP Section 713.04). If a reply to the last Office action has already been filed, APPLICANT IS GIVEN A NON-EXTENDABLE PERIOD OF THE LONGER OF ONE MONTH OR THIRTY DAYS FROM THIS INTERVIEW DATE, OR THE MAILING DATE OF THIS INTERVIEW SUMMARY FORM, WHICHEVER IS LATER, TO FILE A STATEMENT OF THE SUBSTANCE OF THE INTERVIEW. See Summary of Record of Interview requirements on reverse side or on attached sheet.

  
**MARIANNE PADGETT**  
**PRIMARY EXAMINER**

Examiner Note: You must sign this form unless it is an Attachment to a signed Office action.

\_\_\_\_\_  
Examiner's signature, if required

Continuation of Substance of Interview including description of the general nature of what was agreed to if an agreement was reached, or any other comments:

Discussed issues as set forth in the attached e-mail from Jon Guay. Particularly noted that inclusion of the limitations of claims 176-180 in their independent claims would correct the 112, second paragraph problem set forth in section 1 of the action mailed 11/17/2006, and would also appear to correct the first paragraph 112 problems set forth in section 2, however the phrasing of claims so amended would need to be reviewed to determine definitively whether or not all possible 112 first issues had been sufficiently eliminated. Assuming that such an amendment removed all 112 first second problems, it appears that pending an updated search, these claims would be allowable as dependent claims 176-180 were not included in the obviousness double patenting rejection, so that this rejection would also be overcome by such an amendment.

With respect to claims 140, 153 & 164, it was noted that the claims of 6,261,856, such as claims 27-28, recite a gate insulating film on semiconductor islands, where the presence of specific ion blocking films are claimed, but does not specify either positively or negatively that the gate insulating films are covering the ion blocking film, however why the presence or the lack of the gate insulator over the ion blocking film makes a critical difference would need to be sufficiently shown to overcome the obviousness double patenting rejection.

With respect to claims 71, 76 & 164-165, the need for showing what was critical of that "said peripheral circuit" was discussed, as well as some inclusion discussing exactly what the term "peripheral circuit" means in the art.

A handwritten signature in black ink, appearing to be 'MJP', located in the lower right quadrant of the page.

**Padgett, Marianne**

*attachment to Interview Summary*  
*6/6/07*

**From:** Guay, John [jguay@nixonpeabody.com]  
**Sent:** Wednesday, June 06, 2007 2:13 AM  
**To:** Padgett, Marianne  
**Subject:** U.S. 08/169,127 Personal Interview June 6, 2007

Dear Examiner Padgett,

For your review prior to the interview today, we have provided items, below, which we would like to discuss. We look forward to meeting with you at 10:30 AM.

Attendees:

Jeff Costellia Registration No. 35,483  
Kunitaka Yamamoto (SEL)  
John F. Guay Registration No. 47,248

Sincerely,

John Guay

John F. Guay  
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This email message and any attachments are confidential. If you are not the intended recipient, please immediately reply to the sender and delete the message from your email system. Thank you.

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1) The Rejection of Claims 176-180 Under 35 USC 112, First Paragraph

Claims 176-180 are rejected only under Section 112, first paragraph.

Each of claims 176-180 recite the feature of "wherein said insulating layer comprising silicon oxide is formed before the irradiating with the condensed laser beam."

With respect to claims 176-180, the Office Action includes the statement, "Also, new claims 176-180 are lacking with respect to their relationship of where they reside during crystallization, i.e., as an intervening layer between the irradiation source and the semiconductor layer. While the claims are

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inclusive of this option, they are not restricted [thereto] as exemplified above, hence [the claims] still encompass options not supported by the more specific disclosure of the specification." (See, page 3, the first full paragraph).

However, the rejection appears improper because consideration has not been given to "the whole" of each of the claims. More specifically, each of claims 61, 71, 144, 151 and 168, from which dependent claims 176-180 respectively depend, specifically recite that the oxide is removed from "an upper surface of the crystallized layer." The combination of these features with features of forming the insulating layer comprising silicon oxide before crystallization is fully supported by an exemplary embodiment described in the specification. (See, the last line of page 10 to the first line of page 12.)

Furthermore, where the oxide layer resides during crystallization is implicit from claims 176-180 (i.e., "upper surface" of the semiconductor layer).

## 2): The Obviousness-Type Double Patenting Rejection

With respect to independent claims 140, 153 and 164, the Office Action does not address claimed feature of "forming a gate insulating film on said plurality of semiconductor islands wherein said gate insulating film covers a surface of the ion blocking film, said surface being exposed between the plurality of semiconductor islands" is not addressed in the Office Action. Furthermore, the Shinohara et al. patent claims fail to teach or suggest this feature.

With respect to independent claims 71, 76, 164 and 165, each of these claims recite "forming a plurality of thin film transistors ... for the active matrix circuit and said peripheral circuit." The claimed features relating to a "peripheral circuit" is not recited in the Shinohara patent claims, and the Office Action does not address why these features would have been obvious in view of the Shinohara et al. claims.